IN THE CLAIMS:

1. (Withdrawn) A light emitting device comprising:

a thin film transistor on an insulator;

an interlayer insulating film on the thin film transistor;

a first insulating film on the interlayer insulating film;

an anode on the first insulating film;

a wiring line for electrically connecting the thin film transistor to the anode;

a bank over the first insulating film, edge portions of the anode, and wiring;

a second insulating film on the anode and the bank;

an organic compound layer over the anode with the second insulating film interposed therebetween; and

a cathode on the organic compound layer,

wherein the first insulating film is a cured film formed by plasma treatment, and comprises one or more kinds of gas elements selected from the group consisting of hydrogen, nitrogen, halogenated carbon, hydrogen fluoride, and rare gas.

2. (Withdrawn) A light emitting device according to claim 1, wherein the average surface roughness (Ra) of a surface of the anode is 0.9 nm or lower.

3. (Withdrawn) A light emitting device according to claim 1, wherein the bank has on its surface a cured film formed by plasma treatment and comprising one or more kinds of gas elements selected from the group consisting of hydrogen, nitrogen, halogenated carbon, hydrogen fluoride, and rare gas.

4. (Withdrawn) A light emitting device comprising:

a thin film transistor on an insulator;

an interlayer insulating film on the thin film transistor;

a first insulating film on the interlayer insulating film;

an anode on the first insulating film;

a wiring line for electrically connecting the thin film transistor to the anode;

a bank over the first insulating film, edge portions of the anode, and wiring;

a second insulating film on the anode and the bank;

an organic compound layer over the anode with the second insulating film interposed therebetween; and

a cathode on the organic compound layer,

wherein the first insulating film is a DLC film.

5. (Withdrawn) A light emitting device according to claim 4, wherein the average surface roughness (Ra) of a surface of the anode is 0.9 nm or lower.

6. (Withdrawn) A light emitting device according to claim 4, wherein the bank has on its surface a cured film formed by plasma treatment and comprising one or more kinds of gas elements selected from the group consisting of hydrogen, nitrogen, halogenated carbon, hydrogen fluoride, and rare gas.

7. (Withdrawn) A light emitting device comprising:

a thin film transistor on an insulator;

an interlayer insulating film on the thin film transistor;

a first insulating film on the interlayer insulating film;

an anode on the first insulating film;

a wiring line for electrically connecting the thin film transistor to the anode;

a bank over the first insulating film, edge portions of the anode, and wiring;

a second insulating film on the anode and the bank;

an organic compound layer over the anode with the second insulating film interposed therebetween; and

a cathode on the organic compound layer,

wherein the first insulating film is a silicon nitride film.

8. (Withdrawn) A light emitting device according to claim 7, wherein the average surface roughness (Ra) of a surface of the anode is 0.9 nm or lower.

9. (Withdrawn) A light emitting device according to claim 7, wherein the bank has on its surface a cured film formed by plasma treatment and comprising one or more kinds of gas elements selected from the group consisting of hydrogen, nitrogen, halogenated carbon, hydrogen fluoride, and rare gas.

10. (Withdrawn) A light emitting device comprising:

a thin film transistor on an insulator;

an interlayer insulating film on the thin film transistor;

a first insulating film on the interlayer insulating film;

an anode on the first insulating film;

a wiring line for electrically connecting the thin film transistor to the anode;

a bank over the first insulating film, edge portions of the anode, and wiring;

a second insulating film on the anode and the bank;

an organic compound layer above the over with the second insulating film interposed therebetween; and

a cathode on the organic compound layer,

wherein the first insulating film comprises a cured film formed by plasma treatment and a DLC film.

11. (Withdrawn) A light emitting device according to claim 10, wherein the average surface roughness (Ra) of a surface of the anode is 0.9 nm or lower.

12. (Withdrawn) A light emitting device according to claim 10, wherein the bank has on its surface a cured film formed by plasma treatment and comprising one or more kinds of gas elements selected from the group consisting of hydrogen, nitrogen, halogenated carbon, hydrogen fluoride, and rare gas.

13. (Withdrawn) A light emitting device comprising:

a thin film transistor on an insulator;

an interlayer insulating film on the thin film transistor;

a first insulating film on the interlayer insulating film;

an anode on the insulating film;

a wiring line for electrically connecting the thin film transistor to the anode;

a bank over the first insulating film, edge portions of the anode, and wiring;

a second insulating film on the anode and the bank;

an organic compound layer over the anode with the second insulating film interposed therebetween; and

a cathode on the organic compound layer,

wherein the first insulating film is a cured film formed by plasma treatment and a silicon nitride film.

14. (Withdrawn) A light emitting device according to claim 13, wherein the average surface roughness (Ra) of a surface of the anode is 0.9 nm or lower.

15. (Withdrawn) A light emitting device according to claim 13, wherein the bank has on its surface a cured film formed by plasma treatment and comprising one or more kinds of gas elements selected from the group consisting of hydrogen, nitrogen, halogenated carbon, hydrogen fluoride, and rare gas.

16. (Withdrawn) A light emitting device comprising:

a thin film transistor on an insulator;

an interlayer insulating film on the thin film transistor;

a first insulating film on the interlayer insulating film;

an anode on the insulating film;

a wiring line for electrically connecting the thin film transistor to the anode;

a bank over the first insulating film, edge portions of the anode, and wiring;

a second insulating film on the bank;

an organic compound layer on the anode and the bank and

a cathode on the organic compound layer,

wherein the second insulating film is a silicon nitride film.

17. (Withdrawn) A light emitting device according to claim 16, wherein the average surface roughness (Ra) of a surface of the anode is 0.9 nm or lower.

18. (Withdrawn) A light emitting device according to claim 16, wherein the bank has on its surface a cured film formed by plasma treatment and comprising one or more kinds of gas elements selected from the group consisting of hydrogen, nitrogen, halogenated carbon, hydrogen fluoride, and rare gas.

19. (Withdrawn) A device comprising:

a thin film transistor on an insulator;

a first interlayer insulating film over the thin film transistor;

an electrode over the first interlayer insulating film;

a wiring line for electrically connecting the thin film transistor to the electrode, over the first interlayer insulating film;

a second interlayer insulating film over the first interlayer insulating film, the 15 electrode, and the wiring line; and

an anti-electrostatic film over the second interlayer insulating film.

20. (Withdrawn) A light emitting device according to claim 19, wherein the electrode is an anode or a cathode.

21. (Withdrawn) A method of manufacturing a device according to claim 19, wherein the film an organic conductive material comprises selected from the group consisting of polyethylene dioxythiophene, polyaniline, glycerin fatty acid ester, polyoxyethylene alkyl ether, N-2-Hydroxyethyl-N-2-hydroxyalkylamine [hydroxyalkyl monoethanolamine], N,N-Bis(2-hydroxyethyl)alkylamine [alkyl diethanolamine], alkyl diethanolamide, polyoxyethylene alkylamine, polyoxyethylene alkylamine fatty acid ester, alkyl sulfonate, alkylbenzenesulfonate, alkyl phosphate, tetraalkylammonium salt, trialkylbenzyl ammonium salt, alkyl betaine, alkyl imidazolium betaine, and polyoxyethylene alkylphenyl ether.

22. (Withdrawn) A light emitting device according to claim 21, wherein the organic conductive material is formed by spin coating or evaporation.

23. (Withdrawn) A light emitting device according to claim 19, wherein the anti-electrostatic film comprises an organic insulating material selected from the group consisting of polyimide, acrylic, polyamide, polyimideamide, or benzocyclobutene.

24. (Withdrawn) A semiconductor device according to claim 19, wherein the device further comprises an organic compound layer over the second interlayer insulating film and a cathode on the organic compound layer.

25-49. (Canceled)

50. (Currently Amended) A method of manufacturing a device comprising the steps of:

forming a thin film transistor formed over a substrate having an insulating surface;

forming an interlayer insulating film over the thin film transistor;

forming ~~an electrode~~ a wiring over the interlayer insulating film;

forming a ~~wiring line~~ pixel electrode connecting the ~~electrode~~ wiring with the thin film transistor, over the interlayer insulating film;

forming a resin insulating film over ~~the electrode,~~ the wiring ~~line~~ , the pixel electrode, and the interlayer insulating film;

forming a protective film over the resin insulating film;

moving the substrate over which the thin film transistor is formed from a first processing room to a second processing room;

removing the protective film;

etching the resin insulating film to expose said pixel electrode;

forming a light emitting layer over said pixel electrode after said etching, wherein said steps of removing, etching and forming a light emitting layer are performed in said second processing room.

51. (Currently Amended) A method of manufacturing a device according to claim 50, wherein the pixel electrode is an anode or a cathode.

52. (Currently Amended) A method of manufacturing a device comprising the steps of:

forming a thin film transistor formed over a substrate having an insulating surface;

forming an interlayer insulating film over the thin film transistor;

forming ~~an electrode~~ a wiring over the interlayer insulating film;

forming a ~~wiring line~~ pixel electrode connecting the ~~electrode~~ wiring with the thin film transistor, over the interlayer insulating film;

forming a resin insulating film over the ~~anode,~~ the wiring, ~~line~~ the pixel electrode and the interlayer insulating film;

forming a protective film for preventing the substrate over which the thin film transistor is formed from a contamination and an electrostatic discharge damage;

removing the protective film;

etching the resin insulating film to expose said pixel electrode;

forming a light emitting layer over said pixel electrode.

53. (Currently Amended) A method of manufacturing a device according to claim 52, wherein the pixel electrode is an anode or a cathode.

54. (Currently Amended) A method of manufacturing a device according to claim 52, wherein the protective film for preventing the substrate from contamination and electrostatic discharge damage is an organic conductive material selected from the group consisting of polyethylene dioxythiophene, polyaniline, glycerin fatty acid ester, polyoxyethylene alkyl ether, N-2-Hydroxyethyl-N-2-hydroxyalkylamine [hydroxyalkylmonoethanolamine], N,N-Bis(2-hydroxyethyl)alkylamine [alkyl diethanolamine], alkyl diethanolamide, polyoxyethylene alkylamine, polyoxyethylene alkylamine fatty acid ester, alkyl sulfonate, alkylbenzenesulfonate, alkyl phosphate, tetraalkylammonium salt, trialkylbenzylam monium salt, alkyl betaine, alkyl imidazolium betaine, and polyoxyethylene alkylphenyl ether.

55. (Currently Amended) A method of manufacturing a device according to claim 54, wherein the protective film for preventing the substrate from contamination and electrostatic discharge damage is an organic conductive material is formed by spin coating or evaporation.

56. (Currently Amended) A method of manufacturing a device according to claim 52, wherein the protective film for preventing the substrate from contamination and electrostatic discharge damage comprises an organic insulating material selected from the group consisting of polyimide, acrylic, polyamide, polyimideamide, or benzocyclobutene.

57. (Currently Amended) A method of manufacturing a device according to claim 53, wherein the method further comprises the steps of ~~removing the film, etching the resin insulating film to form a bank,~~ wiping the ~~anode~~ pixel electrode, forming an organic compound layer over ~~the bank and~~ the ~~anode~~ pixel electrode.

58. (Previously presented) A method of manufacturing a light emitting device comprising the steps of:

removing an anti-electrostatic film formed on a resin insulating film, the resin insulating film formed over a thin film transistor and anode;

etching the resin insulating film to form a bank;

baking the bank in a vacuum;

forming an organic compound layer over the bank and the anode;

forming a cathode on the organic compound layer.

59. (Previously presented) A method of manufacturing a light emitting device according to claim 58, wherein the film for preventing the substrate from contamination and electrostatic discharge damage is an organic conductive material selected from the group consisting of polyethylene dioxythiophene, polyaniline, glycerin fatty acid ester, polyoxyethylene alkyl ether, N-2-Hydroxyethyl-N-2-hydroxyalkylamine [hydroxyalkyl monoethanolamine], N,N-Bis(2-hydroxyethyl)alkylamine [alkyl diethanolamine], alkyl diethanolamide, polyoxyethylene alkylamine, polyoxyethylene alkylamine fatty acid ester, alkyl sulfonate,
alkylbenzenesulfonate, alkyl phosphate, tetraalkylammonium salt, trialkylbenzylam monium salt, alkyl betaine, alkyl imidazolium betaine, and polyoxyethylene alkylphenyl ether,

60. (Previously presented) A method of manufacturing a device according to claim 59, wherein the organic conductive material is formed by spin coating or evaporation.

61. (Original) A method of manufacturing a device according to claim 58, wherein the anti-electrostatic film comprises an organic insulating material selected from the group consisting of polyimide, acrylic, polyamide, polyimideamide, or benzocyclobutene.

62. (Currently Amended) A method of manufacturing a light emitting device comprising the steps of:

forming a thin film transistor formed over a substrate having an insulating surface;

forming an interlayer insulating film over the thin film transistor;

forming ~~an electrode~~ a wiring over the interlayer insulating film;

forming a ~~wiring line~~ pixel electrode connecting to the ~~electrode~~ wiring over the interlayer insulating film;

forming a resin insulating film over ~~the electrode,~~ the wiring, ~~line~~ the pixel electrode and the interlayer insulating film; and

forming a film over the resin insulating film, the film preventing the substrate over which the thin film transistor is formed from a contamination and an electrostatic discharge damage;

moving the substrate over which the thin film transistor is formed from a first processing room to a second processing room,

removing the film;

etching the resin insulating film to expose said pixel electrode;

forming a light emitting layer over said pixel electrode after said etching, wherein said steps of removing, etching and forming a light emitting layer are performed in said second processing room.

63. (Previously presented) A method of manufacturing a light emitting device according to claim 62, wherein the film comprises an organic conductive material selected from the group consisting of polyethylene dioxythiophene, polyaniline, glycerin fatty acid ester, polyoxyethylene alkyl ether, N-2-Hydroxyethyl-N-2-hydroxyalkylamine [hydroxyalkyl monoethanolamine], N,N-Bis(2-hydroxyethyl)alkylamine [alkyl diethanolamine], alkyl diethanolamide, polyoxyethylene alkylamine, polyoxyethylene alkylamine fatty acid ester, alkyl sulfonate,
alkylbenzenesulfonate, alkyl phosphate, tetraalkylammonium salt, trialkylbenzylam monium salt, alkyl betaine, alkyl imidazolium betaine, and polyoxyethylene alkylphenyl.

64. (Previously presented) A method of manufacturing a light emitting device according to claim 62, wherein the film comprises an organic insulating material selected from the group consisting of polyimide, acrylic, polyamide, polyimideamide, or benzocyclobutene.

65. (Currently Amended) A method of manufacturing a light emitting device comprising the steps of:

forming a thin film transistor formed over a substrate having an insulating surface;

forming an interlayer insulating film over the thin film transistor;

forming a ~~first electrode~~ wiring over the interlayer insulating film;

forming a ~~wiring line~~ pixel electrode connecting to the ~~first electrode~~ wiring over the interlayer insulating film;

forming a resin insulating film over ~~the first electrode,~~ the wiring, ~~line~~ the pixel electrode, and the interlayer insulating film;

forming a film over the resin insulating film, the film preventing the substrate over which the thin film transistor is formed from a contamination and an electrostatic discharge damage;

moving the substrate over which the thin film transistor is formed from a first processing room to a second processing room;

removing the film;

etching the resin insulating film to form a bank;

baking the bank in a vacuum;

forming an organic compound layer over the bank and the first electrode;

forming a second electrode on the organic compound layer.

66. (Previously presented) A method of manufacturing a light emitting device according to claim 65, wherein the film comprises an organic conductive material selected from the group consisting of polyethylene dioxythiophene, polyaniline, glycerin fatty acid ester, polyoxyethylene alkyl ether, N-2-Hydroxyethyl-N-2-hydroxyalkylamine [hydroxyalkyl monoethanolamine], N,N-Bis(2-hydroxyethyl)alkylamine [alkyl diethanolamine], alkyl diethanolamide, polyoxyethylene alkylamine, polyoxyethylene alkylamine fatty acid ester, alkyl sulfonate,
alkylbenzenesulfonate, alkyl phosphate, tetraalkylammonium salt, trialkylbenzylam monium salt, alkyl betaine, alkyl imidazolium betaine, and polyoxyethylene alkylphenyl.

67. (Previously presented) A method of manufacturing a light emitting device according to claim 65, wherein the film comprises an organic insulating material selected from the group consisting of polyimide, acrylic, polyamide, polyimideamide, or benzocyclobutene.

68. (Currently Amended) A method of manufacturing a light emitting device comprising the steps of:

forming a thin film transistor formed over a substrate having an insulating surface;

forming an interlayer insulating film over the thin film transistor;

forming ~~an electrode~~ a wiring over the interlayer insulating film;

forming a ~~wiring line~~ pixel electrode connecting the ~~electrode~~ wiring over the interlayer insulating film;

forming a resin insulating film over the ~~anode, the wiring line~~ wiring, the pixel electrode and the interlayer insulating film;

after forming the resin insulating film over the ~~anode, the wiring line~~ wiring, the pixel electrode and the interlayer insulating film, forming a film comprising an organic conductive material over the resin insulating film, the film preventing the substrate over which the thin film transistor is formed from a contamination and an electrostatic discharge damage.

69. (Previously presented) A method of manufacturing a light emitting device according to claim 68, wherein the organic conductive material is selected from the group consisting of polyethylene dioxythiophene, polyaniline, glycerin fatty acid ester, polyoxyethylene alkyl ether, N-2-Hydroxyethyl-N-2-hydroxyalkylamine [hydroxyalkyl monoethanolamine], N,N-Bis(2-hydroxyethyl)alkylamine [alkyl diethanolamine], alkyl diethanolamide, polyoxyethylene alkylamine, polyoxyethylene alkylamine fatty acid ester, alkyl sulfonate,
alkylbenzenesulfonate, alkyl phosphate, tetraalkylammonium salt, trialkylbenzylam monium salt, alkyl betaine, alkyl imidazolium betaine, and polyoxyethylene alkylphenyl.

70. (Currently Amended) A method of manufacturing a light emitting device comprising the steps of:

forming a thin film transistor formed over a substrate having an insulating surface;

forming an interlayer insulating film over the thin film transistor;

forming ~~an electrode~~ a wiring over the interlayer insulating film;

forming a ~~wiring line~~ pixel electrode connecting to the ~~electrode~~ wiring over the interlayer insulating film;

forming a resin insulating film over ~~the electrode,~~ the wiring ~~line~~ , the pixel electrode, and the interlayer insulating film; and

after forming the resin insulating film over ~~the electrode,~~ the wiring ~~line~~ , the pixel electrode, and the interlayer insulating film, forming a film comprising an organic conductive material over the resin insulating film, the film preventing the substrate over which the thin film transistor is formed from a contamination and an electrostatic discharge damage;

after forming the film comprising the organic conductive material, moving the substrate over which the thin film transistor is formed from a first processing room to a second processing room.

71. (Previously presented) A method of manufacturing a light emitting device according to claim 70, wherein the organic conductive material is selected from the group consisting of polyethylene dioxythiophene, polyaniline, glycerin fatty acid ester, polyoxyethylene alkyl ether, N-2-Hydroxyethyl-N-2-hydroxyalkylamine [hydroxyalkyl monoethanolamine], N,N-Bis(2-hydroxyethyl)alkylamine [alkyl diethanolamine], alkyl diethanolamide, polyoxyethylene alkylamine, polyoxyethylene alkylamine fatty acid ester, alkyl sulfonate,
alkylbenzenesulfonate, alkyl phosphate, tetraalkylammonium salt, trialkylbenzylam monium salt, alkyl betaine, alkyl imidazolium betaine, and polyoxyethylene alkylphenyl.

72. (Currently Amended) A method of manufacturing a light emitting device comprising the steps of:

forming a thin film transistor formed over a substrate having an insulating surface;

forming an interlayer insulating film over the thin film transistor;

forming a ~~first electrode~~ wiring over the interlayer insulating film;

forming a ~~wiring line~~ first electrode connecting to the ~~first electrode~~ wiring over the interlayer insulating film;

forming a resin insulating film over ~~the first electrode,~~ the wiring ~~line~~ , the first electrode, and the interlayer insulating film;

after forming the resin insulating film over ~~the electrode,~~ the wiring ~~line~~ , the first electrode, and the interlayer insulating film, forming a film comprising an organic conductive material over the resin insulating film, the film preventing the substrate over which the thin film transistor is formed from a contamination and an electrostatic discharge damage;

after forming the film comprising the organic conductive material, moving the substrate over which the thin film transistor is formed from a first processing room to a second processing room;

removing the film;

etching the resin insulating film to form a bank;

baking the bank in a vacuum;

forming an organic compound layer over the bank and the first electrode;

forming a second electrode on the organic compound layer.

73. (Previously presented) A method of manufacturing a light emitting device according to claim 72, wherein the organic conductive material is selected from the group consisting of polyethylene dioxythiophene, polyaniline, glycerin fatty acid ester, polyoxyethylene alkyl ether, N-2-Hydroxyethyl-N-2-hydroxyalkylamine [hydroxyalkyl monoethanolamine], N,N-Bis(2-hydroxyethyl)alkylamine [alkyl diethanolamine], alkyl diethanolamide, polyoxyethylene alkylamine, polyoxyethylene alkylamine fatty acid ester, alkyl sulfonate,
alkylbenzenesulfonate, alkyl phosphate, tetraalkylammonium salt, trialkylbenzylam monium salt, alkyl betaine, alkyl imidazolium betaine, and polyoxyethylene alkylphenyl.

74. (Currently Amended) A method of manufacturing a light emitting device comprising the steps of:

forming a thin film transistor formed over a substrate having an insulating surface;

forming an interlayer insulating film over the thin film transistor;

forming ~~an electrode~~ a wiring over the interlayer insulating film;

forming a ~~wiring line~~ pixel electrode connecting the ~~electrode~~ wiring over the interlayer insulating film;

forming a resin insulating film over ~~the anode,~~ the wiring ~~line~~ , the pixel electrode, and the interlayer insulating film;

forming a film comprising an organic insulating material over the resin insulating film, the film preventing the substrate over which the thin film transistor is formed from a contamination and an electrostatic discharge damage.

75. (Previously presented) A method of manufacturing a light emitting device according to claim 74, wherein the organic insulating material is selected from the group consisting of polyimide, acrylic, polyamide, polyimideamide, or benzocyclobutene.

76. (Currently Amended) A method of manufacturing a light emitting device comprising the steps of:

forming a thin film transistor formed over a substrate having an insulating surface;

forming an interlayer insulating film over the thin film transistor;

forming ~~an electrode~~ a wiring over the interlayer insulating film;

forming a ~~wiring line~~ pixel electrode connecting to the ~~electrode~~ wiring over the interlayer insulating film;

forming a resin insulating film over ~~the electrode,~~ the wiring ~~line~~ , the pixel electrode, and the interlayer insulating film; and

forming a film comprising an organic insulating material over the resin insulating film, the film preventing the substrate over which the thin film transistor is formed from a contamination and an electrostatic discharge damage;

moving the substrate over which the thin film transistor is formed from a first processing room to a second processing room.

77. (Previously presented) A method of manufacturing a light emitting device according to claim 76, wherein the organic insulating material is selected from the group consisting of polyimide, acrylic, polyamide, polyimideamide, or benzocyclobutene.

78. (Currently Amended) A method of manufacturing a light emitting device comprising the steps of:

forming a thin film transistor formed over a substrate having an insulating surface;

forming an interlayer insulating film over the thin film transistor;

forming a ~~first electrode~~ wiring over the interlayer insulating film;

forming a ~~wiring line~~ first electrode connecting to the ~~first electrode~~ wiring over the interlayer insulating film;

forming a resin insulating film over ~~the first electrode,~~ the wiring ~~line~~ , the first electrode, and the interlayer insulating film;

forming a film comprising an organic insulating material over the resin insulating film, the film preventing the substrate over which the thin film transistor is formed from a contamination and an electrostatic discharge damage;

moving the substrate over which the thin film transistor is formed from a first processing room to a second processing room;

removing the film;

etching the resin insulating film to form a bank;

baking the bank in a vacuum;

forming an organic compound layer over the bank and the first electrode;

forming a second electrode on the organic compound layer.

79. (Previously presented) A method of manufacturing a light emitting device according to claim 78, wherein the organic insulating material is selected from the group consisting of polyimide, acrylic, polyamide, polyimideamide, or benzocyclobutene.

80. (Currently Amended) A method of manufacturing a light emitting device comprising the steps of:

forming a thin film transistor formed over a substrate having an insulating surface;

forming an interlayer insulating film over the thin film transistor;

performing plasma treatment on a surface of the interlayer insulating film;

forming a contact hole in the interlayer insulating film after performing the plasma treatment;

forming ~~an electrode~~ a wiring over the interlayer insulating film;

forming a ~~wiring line~~ pixel electrode connecting to the ~~electrode~~ wiring over the interlayer insulating film;

forming a resin insulating film over ~~the electrode,~~ the wiring ~~line~~ , the pixel electrode, and the interlayer insulating film; and

forming a film over the resin insulating film, the film preventing the substrate over which the thin film transistor is formed from a contamination and an electrostatic discharge damage;

moving the substrate over which the thin film transistor is formed from a first processing room to a second processing room.

81. (Previously presented) A method of manufacturing a light emitting device according to claim 80, wherein the film comprises an organic conductive material selected from the group consisting of polyethylene dioxythiophene, polyaniline, glycerin fatty acid ester, polyoxyethylene alkyl ether, N-2-Hydroxyethyl-N-2-hydroxyalkylamine [hydroxyalkyl monoethanolamine], N,N-Bis(2-hydroxyethyl)alkylamine [alkyl diethanolamine], alkyl diethanolamide, polyoxyethylene alkylamine, polyoxyethylene alkylamine fatty acid ester, alkyl sulfonate, alkylbenzenesulfonate, alkyl phosphate, tetraalkylammonium salt, trialkylbenzylam monium salt, alkyl betaine, alkyl imidazolium betaine, and polyoxyethylene alkylphenyl.

82. (Previously presented) A method of manufacturing a light emitting device according to claim 80, wherein the film comprises an organic insulating material selected from the group consisting of polyimide, acrylic, polyamide, polyimideamide, or benzocyclobutene.